

Tobias Ohrdes

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

697
citations

933447

10
h-index

1058476

14
g-index

20
all docs

20
docs citations

20
times ranked

664
citing authors

#	ARTICLE	IF	CITATIONS
1	Recombination behavior and contact resistance of n+ and p+ poly-crystalline Si/mono-crystalline Si junctions. <i>Solar Energy Materials and Solar Cells</i> , 2014, 131, 85-91.	6.2	195
2	Ion Implantation for Poly-Si Passivated Back-Junction Back-Contacted Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2015, 5, 507-514.	2.5	131
3	Charge carrier lifetime degradation in Cz silicon through the formation of a boron-rich layer during BBr ₃ diffusion processes. <i>Semiconductor Science and Technology</i> , 2010, 25, 055001.	2.0	82
4	A numerical simulation study of gallium-phosphide/silicon heterojunction passivated emitter and rear solar cells. <i>Journal of Applied Physics</i> , 2014, 115, 044508.	2.5	49
5	Injection dependence of the effective lifetime of n-type Si passivated by Al ₂ O ₃ : An edge effect?. <i>Solar Energy Materials and Solar Cells</i> , 2014, 120, 436-440.	6.2	42
6	The effect of sample edge recombination on the averaged injection-dependent carrier lifetime in silicon. <i>Journal of Applied Physics</i> , 2012, 111, 054508.	2.5	41
7	Dataset on electrical single-family house and heat pump load profiles in Germany. <i>Scientific Data</i> , 2022, 9, 56.	5.3	22
8	Characterisation and implications of the boron rich layer resulting from open-tube liquid source BBR ₃ boron diffusion processes. , 2009, , .		19
9	Aluminum-oxide-based inversion layer solar cells on n-type crystalline silicon: Fundamental properties and efficiency potential. <i>Journal of Applied Physics</i> , 2014, 115, 073702.	2.5	19
10	Building blocks for back-junction back-contacted cells and modules with ion-implanted poly-Si junctions. , 2014, , .		18
11	Influence of the boron emitter profile on V _{OC} and J _{SC} losses in fully ion implanted n-type PERT solar cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 291-297.	1.8	16
12	Emitter recombination current densities of boron emitters with silver/aluminum pastes. , 2014, , .		13
13	Electrical and Structural Analysis of Crystal Defects After High-Temperature Rapid Thermal Annealing of Highly Boron Ion-Implanted Emitters. <i>IEEE Journal of Photovoltaics</i> , 2015, 5, 166-173.	2.5	13
14	Counterdoping with patterned ion implantation. , 2013, , .		11
15	19% Efficient Thin-Film Crystalline Silicon Solar Cells From Layer Transfer Using Porous Silicon: A Loss Analysis by Means of Three-Dimensional Simulations. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 909-917.	3.0	10
16	Structural analysis of textured silicon surfaces after ion implantation under tilted angle. <i>Semiconductor Science and Technology</i> , 2014, 29, 095004.	2.0	7
17	Solar cell emitter design with PV-tailored implantation. <i>Energy Procedia</i> , 2011, 8, 167-173.	1.8	6
18	Structural investigation of ion implantation of boron on random pyramid textured Si(100) for photovoltaic applications. , 2014, , .		2

#	ARTICLE	IF	CITATIONS
19	Conceptual Comparison between Standard Si Solar Cells and back Contacted Cells. Energy Procedia, 2014, 55, 11-16.	1.8	1
20	Overcoming phosphorus emitter limitations in PERC Si solar cells by using a gallium-phosphide heteroemitter. , 2013, , .		0